wherein an amount of sodium contained within the wiring is equal to or less than 0.3

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2. (Amended) A device according to claim 1, wherein a thickness of the tungsten nitride film is 10 to 50 nm and a thickness of the tungsten film is 200 to 400 nm.

3. (Twice Amended) A device according to claim 1, wherein electrical resistivity of the wiring is equal to or less than 40  $\mu\Omega$  cm.

4. (Twice Amended) A semiconductor device comprising:

a wiring formed over a substrate, the wirings comprising a metal film and a nitride film of the metal film, the metal film located on the nitride film,

wherein the wiring includes at least one inert element and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

- 5. (Twice Amended) A device according to claim 4, further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.
- 6. (Twice Amended) A device according to claim 4, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

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7. (Twice Amended) A device according to claim 4, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

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- 9. (Twice Amended) A device according to claim 4, wherein internal stress of the wiring is from -1 x  $10^{10}$  dyn/cm<sup>2</sup> to +1 x  $10^{10}$  dyn/cm<sup>2</sup>.
- 10. (Twice Amended) A device according to claim 4, wherein line width of the wiring is equal to or less than 5  $\mu$ m.



- 11. (Twice Amended) A device according to claim 4, wherein film thickness of the wiring is equal to or greater than 0.1  $\mu$ m, and equal to or less than 0.7  $\mu$ m.
- 12. (Twice Amended) A device according to claim 4, wherein the wiring is used as a gate electrode of a TFT.
- 13. (Twice Amended) A device according to claim 4, wherein resistance value per 1 square  $\mu m$  of surface area of a connection between the wiring and an aluminum wiring is equal to or less than  $40~\Omega$ .

## 16. (Twice Amended) A semiconductor device comprising:



a wiring formed over a substrate, the wiring comprising a tungsten nitride film and a tungsten film formed thereon; and

an insulating film formed over the wiring, said insulating film comprising SiOxNy,

wherein the wiring includes at least one inert element and 90% or more of the inert

cup dlement is argon, and

ppm.

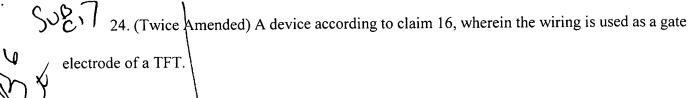
wherein an amount of sodium contained within the wiring is equal to or less than 0.3

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- 17. (Twice Amended) A device according to claim 16, further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.
- 18. (Twice Amended) A device according to claim 16, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.
- 19. (Twice Amended) A device according to claim 16, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.
- 21. (Twice Amended) A device according to claim 16, wherein internal stress of the tungsten film or of the wiring is from -1 x  $10^{10}$  dyn/cm<sup>2</sup> to +1 x  $10^{10}$  dyn/cm<sup>2</sup>.



- 22. (Twice Amended) A device according to claim 16, wherein line width of the wiring is equal to or less than 5 μm.
- 23. (Twice Amended) A device according to claim , wherein film thickness of the wiring is equal to or greater than 0.1  $\mu$ m, and equal to or less than 0.7  $\mu$ m.



25. (Twice Amended) A device according to claim 16, wherein resistance value per 1 square  $\mu m$  of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40  $\Omega$ .

## 28. (Twice Amended) A semiconductor device comprising:

a wiring formed over a substrate having a lamination structure comprising a phosphorus doped silicon, a nitride film of tungsten, and a film comprising tungsten,

wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

36. (Amended) A device according to claim 28, wherein the wiring is used as a gate electrode of a TFT.

## 40. (Twice Amended) A semiconductor device comprising:

a wiring formed over a substrate, the wiring having a lamination structure containing a tungsten nitride film and a film comprising tungsten formed thereon,

wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon,